NEC

PNP SILICON TRANSISTOR 2SA953

DESCRIPTION

The 2SA953 is designed for use in driver stage of high voltage

audio equipment.

FEATURES

• High total power dissipation.

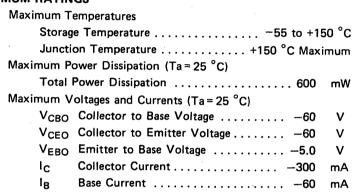
 $P_T = 600 \text{ mW}$

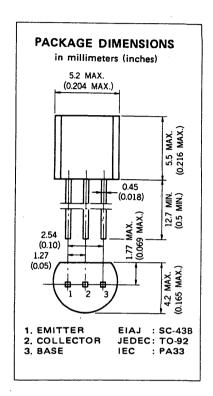
High h_{FE} and high voltage.

 $h_{FE} (I_C = -50 \text{ mA}) : 200 \text{ TYP}.$: -60 V

VCEO

ABSOLUTE MAXIMUM RATINGS





ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1*	DC Current Gain	90	200	400	_	V _{CE} = -1.0 V, I _C = -50 mA
hFE2*	DC Current Gain	30	80		_	V _{CE} = -1.0 V, I _C = -300 mA
c _{ob}	Collector to Base Capacitance		13	25	pF	$V_{CB} = -6.0 \text{ V}, I_E = 0,$ f = 1.0 MHz
f _T	Gain Bandwidth Product	50	100		MHz	V _{CE} = -6.0 V, I _E = 10 mA
V _{BE} *	Base to Emitter Voltage	-600	-660	-700	mV	V _{CE} = -6.0 V, I _C = -10 mA
V _{CE(sat)} *	Collector Saturation Voltage		-0.15	0.6	V	I _C =-300 mA, I _B =-30 mA
V _{BE(sat)} *	Base Saturation Voltage		-0.85	-1.2	· V	IC=-300 mA, IB=-30 mA
Ісво	Collector Cutoff Current			-100	nA	V _{CB} =-60 V, I _E =0
¹ EBO	Emitter Cutoff Current			-100	nΑ	V _{FB} = -5.0 V, I _C = 0

^{*} Pulsed PW \leq 350 μ s, duty cycle \leq $\overline{2.0}$ %

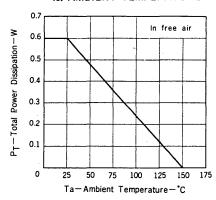
Classification of h_{FE1}

Rank	M	L	κ
Range	90 — 180	135 – 270	200 – 400

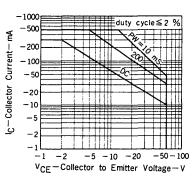
hFE Test Conditions : $V_{CE} = -1.0 \text{ V}$, $I_{C} = -50 \text{ mA}$

TYPICAL CHARACTERISTICS (Ta = 25 °C unless otherwise noted)

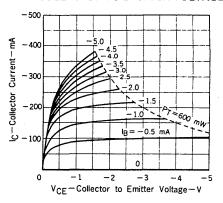
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



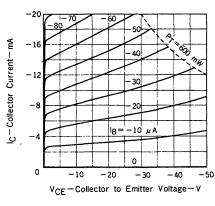
SAFE OPERATING AREAS (TRANSIENT THERMAL RESISTANCE)



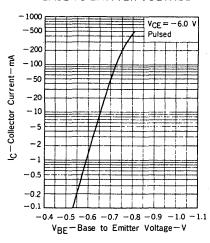
COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE



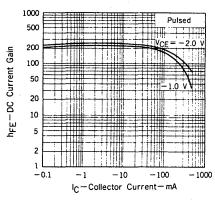
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



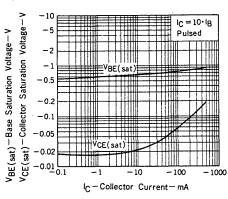
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



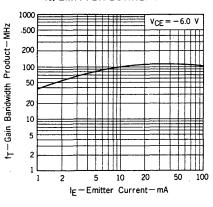
DC CURRENT GAIN vs. COLLECTOR CURRENT



BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



EMITTER TO BASE AND COLLECTOR TO BASE CAPACITANCE vs. REVERSE VOLTAGE

